tion, and device processing and applications. A special session on ultrathin Si/Ge superlattices is planned.

Chairs: E. Kasper, Daimler-Benz A.G., Germany, phone (49) 731-505-2039, fax (49) 731-505-4102; Y. Shiraki, RCAST, Japan, phone (81) 3-3481-4428, fax (81) 3-3485-5135; T.P. Pearsall, University of Washington, USA, phone (1) 206-543-2600, fax (1) 206-543-3100.

Symposium B: Laser, Lamp, and Synchrotron-Assisted Materials Surface Processing

This four-day symposium will cover all aspects of photon-assisted materials surface processing, from basic studies to novel phenomena for applications and devices. Surface, interface and thin film reactions of dielectrics, semiconducotrs and superconductors, metals, organic and biological materials will be emphasized interms of fundamental understanding and assessing the criteria for future practical applications.

Chairs: E.E. Marinero, IBM Almaden Research Labs, USA, phone (1) 408-927-3025; fax (1) 408-927-2077; I. Nishiyama, NEC Opto-Electronics, Japan, phone (81) 298-501169 (or 11), fax (81) 298-566140 (or 31); M. Stuke, Max-Planck-Institut, Germany, phone (49) 551-201-338, fax (49) 551-201-330.

Symposium C: Chemistry for Electronic Materials

This four-day symposium will cover chemistry aspects for all kinds of materials processing used for electronic applications, e.g., Si, III-V compounds, superconductors, and metallization materials. New precursors are of special interest, and presentations will span basic research for fundamental understanding, engineering problems, and future aspects.

Chairs: Y. Pauleau, Inst. National Polytechnique de Grenoble, France, phone (33) 76-88-59-62, fax (33) 76-88-51-30; G. Wahl, Inst. für Oberlachentechnik und Plasmatechnische, Germany, phone (49) 531-391-9401, fax (49) 531-391-9400, K.F. Jensen, MIT, USA, phone (1) 617-253-4589, fax (1) 617-253-9695; T. Hirai, Tohoku University, Japan, phone (81) 22-227-6200, fax (81) 22-215-2107.

Symposium D: Diagnostic Techniques for Semiconductor Materials Analysis and Fabrication Process Control

This symposium aims to bring together researchers working in all areas of semiconductor materials and process characterization. Both basic studies and applications will be highlighted.

Chairs: G.M. Crean, National Microelectronics Research Center, Ireland, phone (353) 21-27-68-71, fax (353) 21-27-02-71; M. Kashiwagi, Toshiba Corporation, Japan, phone (81) 44-549-2317, fax (81) 44-549-2267; R. Stuck, Centre de Recherches Nucleaires, France, phone (33) 88-28-65-43, fax (33) 88-28-09-90; J. Woollam, University of Nebraska, USA, phone (1) 402-472-1964, fax (1) 402-472-7987.

Symposium E. Synthetic Materials for Nonlinear Optics and Electronics

This four-day symposium aims to cover the emerging class of unconventional electronic materials based on organic FET molecules and polymers. General topics include design and synthesis of new materials, characterization, processing, and device applications.

Chairs: C. Taliani, CNR, Italy, phone (39) 51-28-70-02, fax (39) 51-22-50-31; Z.V. Vardeny, University of Utah, USA, phone (1) 801-581-8372, fax (1) 801-581-4801; Y. Maruyama, Institute of Molecular Science, Japan, phone (81) 564-55-7410, fax (81) 564-54-2254.

Symposium F: New Aspects of the Growth, Characterization, and Applications of CdTe and Related Cd-Rich Alloys

This three-day symposium will provide the opportunity to review research devoted to CdTe and related Cd-rich alloys during the last decade since K. Zanio's monograph. It will cover the most recent aspects, ranging from basic studies to novel applications.

Chairs: R. Triboulet, CNRS, France, phone (33) 1-45-07-50-88, fax (33) 1-45-07-58-99; W.R. Wilcox, Charkson University, USA, phone (1) 315-268-6446, fax (1) 315-268-3841; O. Oda, Nippon Mining Co., Japan, phone (81) 484-33-2051, fax (81) 484-45-5400.

Joint Session on Single-Chamber Processing: Requirements and Challenges

This joint session will explore the general aspects and background of integrated processing and present reports on the status of the technology, the design concepts, and relevant equipment. Specific process modules such as deposition chambers, annealing or etching reactors will also be reviewed. Standardization of this equipment will be addressed.

Chairs: Y.I. Nissim, CNET, France, phone (33) 1-42-31-73-19, fax (33) 1-42-53-49-30; A. Katz, AT&T Bell Laboratories, USA, phone (1) 908-582-2261, fax (1) 908-582-4347.

ICAM '93 Planned for Tokyo

The Third International Conference on Advanced Materials (ICAM '93) will be held in Tokyo, Japan, August 31 to September 4, 1993. The ICAM '93 Organizing Committee is being joined in its efforts by MRS-Japan and the International Union of Materials Research Societies. Support is coming from Nikkan Kogyo Shimbun, Ltd.

Just as the first and second conferences (1988 in Tokyo and 1991 in Strasbourg), this conference will cover the entire field of advanced materials with a full complement of symposia. For more information, contact: ICAM'93, c/o Nikkan Kogyo Shimbun, Ltd., Business Bureau, 8-10, Kudan-Kita 1-Chome, Chiyoda-ku, Tokyo 102, Japan; phone 81-3-3222-7162; fax 81-3-3221-7137.

ICAM '93 Chairs: Masao Doyama, Masaki Hasegawa, Shigeyuki Sōmiya, and Shigehiko Yamada.

Tentative List of Symposia: Composites; Glassy Materials; Powder Preparation; Computer Applications in Materials Science and Engineering; Superplastic Phenomena in Ceramics, Intermetallics, and Composites; Materials Interconnection—A Novel Approach to Functional Joining for Dissimilarity Considerations; Corrosion/Coating of Advanced Materials; Shape Memory Materials; Hydrogen Absorbing Materials and Hydride Batteries; Structural Ceramics; Development of Environmentally Conscious Materials; Rare-Earth Iron-Based Permanent Magnet Materials; C_{60} and Related Materials; Biomaterials; Catalytic Materials; Advanced Processing; Ordered Polymers; Photo- and Electro-Responsive Materials; Electronic Materials; Biosensors; Materials Synthesis and Modification by Ion Beams and/or Laser Beams; Materials for Information Storage Media; Fabrication of Silicon-Based Ceramics; Frontiers of Materials Science and Engineering; Diamond and Related Materials; Gradient Materials; Superconducting Materials; Grain Boundaries; Nanophase Materials; Superlattices; Surfaces and Interfaces; Ferro-electric Thin Films; Construction and Functions of Organic Thin Films; Materials for Bioscience and Biotechnology; Microgravity and Materials.

https://doi.org/10.1557/S0883769400040884 Published online by Cambridge University Press